

HD74SSTV16842

11-bit to 22-bit Buffer with SSTL_2 Inputs and Outputs

REJ03D0829-0200

(Previous: ADE-205-602A)

Rev.2.00 Apr 07, 2006

Description

The HD74SSTV16842 is a 11-bit to 22-bit buffer designed for 2.3 V to 2.7 V Vcc operation and SSTL_2 data (A) inputs.

Features

- Supports SSTL_2 data inputs
- Flow through architecture optimizes PCB layout
- Ordering Information

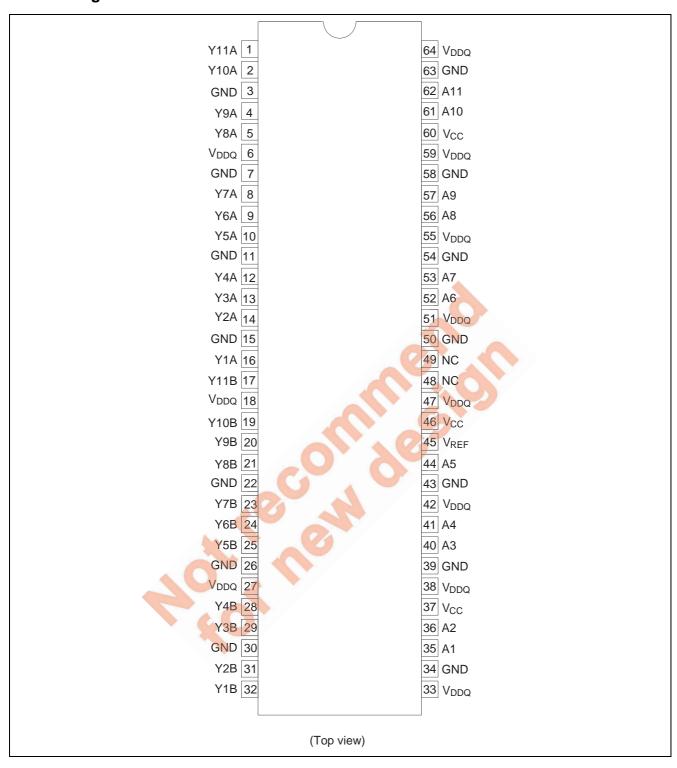
Part Name	Package Type	Package Code (Previous code)	Package Abbreviation	Taping Abbreviation (Quantity)	
HD74SSTV16842TEL	TSSOP-64 pin	PTSP0064KA-A		EL (1,000 pcs / Reel)	
		(TTP-64DV)			

Function Table

Input A	Output Y			
L	L			
Н	Н			

H: High level L: Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CC} or V _{DDQ}	-0.5 to 3.6	V	
Input voltage *1	Vı	-0.5 to V _{DDQ} +0.5	V	
Output voltage *1, 2	Vo	-0.5 to V _{DDQ} +0.5	V	
Input clamp current	I _{IK}	±50	mA	$V_I < 0$ or $V_I > V_{CC}$
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{DDQ}$
Continuous output current	I _O	±50	mA	$V_O = 0$ to V_{DDQ}
V _{CC} , V _{DDQ} or GND current / pin	I _{CC} , I _{DDQ} or I _{GND}	±100	mA	
Maximum power dissipation	P _T	1	W	TSSOP
at Ta = 55°C (in still air)				
Storage temperature	Tstg	-65 to +150	°C	

Notes: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device.

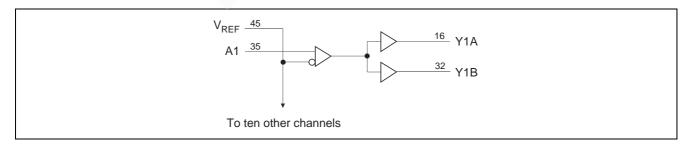
These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This current will flow only when the output is in the high state and $V_0 > V_{DDQ}$.

Recommended Operating Conditions

Item	Symbol	Min	Тур	Max	Unit	Conditions
Supply voltage	Vcc	V_{DDQ}	2.5	2.7	V	
Output supply voltage	V_{DDQ}	2.3	2.5	2.7	V	
Reference voltage	V_{REF}	1.15	1.25	1.35	V	$V_{REF} = 0.5 \times V_{DDQ}$
Termination voltage	V _{TT}	V _{REF} -40 mV	V _{REF}	V _{REF} +40 mV	V	
Input voltage	Vı	0	+0)	V _{CC}	V	
AC high level input voltage	V _{IH}	V _{REF} +310 mV	-	_	V	A
AC low level input voltage	VIL	9/- 3		V _{REF} –310 mV	V	A
DC high level input voltage	VIH	V _{REF} +150 mV	_	_	V	A
DC low level input voltage	V _{IL}		_	V _{REF} -150 mV	V	A
High level output current	loh	4	_	-20	mA	
Low level output current	l _{OL}		_	20	mA	
Input transition rise or fall time	Δt / Δν		_	10	ns/V	
Operating temperature	Та	0	_	70	°C	

Logic Diagram



Electrical Characteristics

Item		Symbol	V _{CC} (V)	Min	Тур	Max	Unit	Test Conditions
Input diode voltage		V _{IK}	2.3	_	_	-1.2	V	$I_{IN} = -18 \text{ mA}$
Output voltage		V _{OH}	2.3 to 2.7	V _{CC} -0.2	_	_	V	I _{OH} = -100 μA
			2.3	1.95	_	V_{DDQ}		I _{OH} = -16 mA
		V _{OL}	2.3 to 2.7	_	_	0.2		I _{OL} = 100 μA
			2.3	0	_	0.35		I _{OL} = 16 mA
Input current	(All inputs)	I _{IN}	2.7	_	_	±5	μΑ	$V_{IN} = 2.7 \text{ V or } 0$
Quiescent supply current		I _{CC} *2	2.7	_	_	45	mA	$V_{IN} = V_{IH(AC)}$ or $V_{IL(AC)}$, $I_O = 0$
Dynamic operating per each		I _{CCD} *2	2.7	_	_	20	μΑ/	$V_I = V_{IH(AC)}$ or $V_{IL(AC)}$,
data input							data	One data input switching at
							input	50% duty cycle.
Output high *3		r _{OH}	2.3 to 2.7	7	_	20	Ω	$I_{OH} = -20 \text{ mA}$
Output low *3		r _{OL}	2.3 to 2.7	7	_	20	Ω	I _{OL} = 20 mA
r _{OH} - r _{OL} each separate bit *3		$r_{O(\Delta)}$	2.5	_	_	4	Ω	$I_0 = 20 \text{ mA}, Ta = 25^{\circ}\text{C}$
	Data inputs	C _{IN}	2.5 *1	2.5	_	3.5	pF	$V_I = V_{REF} \pm 310 \text{ mV}$
capacitance								

Notes: 1. All typical values are at $V_{CC} = 2.5 \text{ V}$, $Ta = 25^{\circ}\text{C}$.

- 2. Total I_{CC} (max) = I_{CC} + { I_{CCD} (Data) × 11}
- 3. This is effective in the case that it did terminate by resistance.

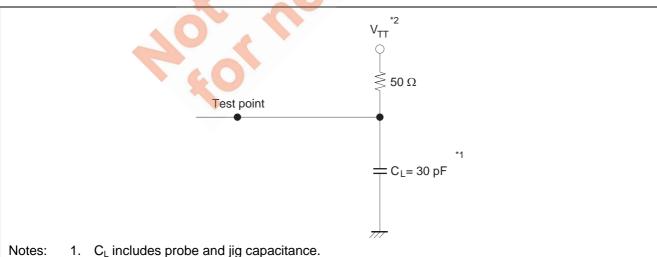
Switching Characteristics

 $V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	$V_{CC} = 2.5 \pm 0.2 \text{ V}$			Unit	FROM	TO
item		Min	Тур	Max	Unit	(Input)	(Output)
Propagation delay time *1	t _{PLH}	1.6	<u> </u>	2.8	ns	А	Υ

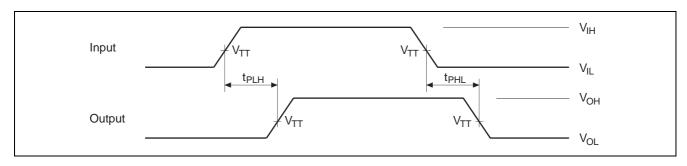
Note: 1. This timing relationship is specified into test load (see waveforms – 1) with all of the outputs switching.

Test Circuit



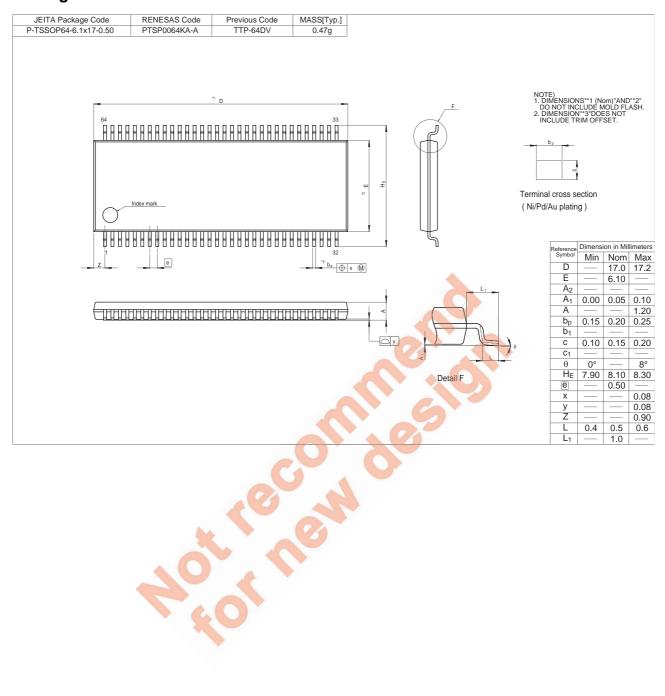
- 1. C_L includes probe and jig capacitance.
- $2. \quad V_{TT} = V_{REF} = V_{DDQ} \times 0.5$
- 3. Input waveform : PRR \leq 10 MHz, Zo = 50 Ω , Input slew rate = 1 V/ns ±20% (unless otherwise noted.)

Waveforms





Package Dimensions



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